
PM4575J

Silicon N-Channel Power MOS FET Module

HITACHI

Application

High Speed Power Switching

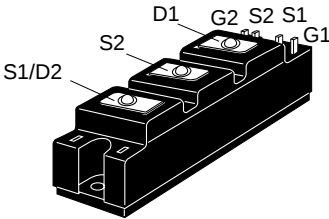
Features

- Equipped with Power MOS FET
- Low on-resistance
- High speed switching
- Low drive current
- Wide area of safe operation
- Inherent parallel diode between source and drain
- Isolated base from Terminal
- Suitable for motor driver, switching regulator and etc.

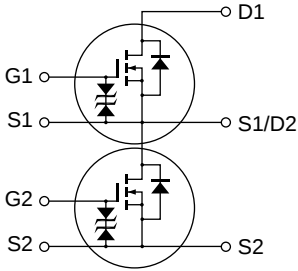
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Outline

LF-J



Equivalent Circuit



No	Electrode	Terminals	Remarks
S1	Source 1	M5 screw	Power terminal
D1	Drain 1	M5 screw	
S2	Source 2	M5 screw	
D2	Drain 2	M5 screw	
G1	Gate 1	#110	Signal terminals
S1	Source 1	#110	
G2	Gate 2	#110	
S2	Source 2	#110	

Absolute Maximum Ratings (Ta = 25°C) (Per FET chip)

Item	Symbol	Rating	Unit
Drain source voltage	$V_{(BR)DSS}$	450	V
Gate source voltage	$V_{(BR)GSS}$	±30	V
Drain current	I_D	75	A
Drain peak current	$I_{D(peak)}$	180	A
Body to drain diode reverse drain current	I_{DR}	75	A
Body to drain diode reverse peak current	$I_{DR(peak)}$	180	A
Channel dissipation	P_{ch}^{*1}	300	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	−45 to +125	°C
Insulation dielectric	V_{iso}^{*2}	2000	Vrms

- Notes: 1. Value at Ta = 25°C
2. Base to terminals AC minute

Electrical Characteristics (Ta = 25°C) (Per FET chip)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	450	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0 \text{ V}$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0 \text{ V}$
Drain leak current	I_{DSS}	—	—	500	μA	$V_{DS} = 360 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate to source threshold voltage	$V_{GS(th)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain to source saturation voltage	$V_{DS(on)}$	—	3.7	4.44	V	$I_D = 37 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.10	0.12	Ω	$I_D = 37 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	—	45	—	S	$I_D = 37 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	9600	—	μF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	2300	—		
Reverse transfer capacitance	C_{rss}	—	330	—		
Turn-on delay time	$t_{d(on)}$	—	100	—	ns	$I_D = 37 \text{ A}$, $V_{GS} = 10 \text{ V}$
Rise time	t_r	—	310	—		$R_g = 50 \Omega$
Turn-off delay time	$t_{d(off)}$	—	550	—		$R_L = 1 \Omega$
Fall time	t_f	—	135	—		
Body to drain diode forward voltage	V_{DF}	—	1.8	—	V	$I_F = 75 \text{ A}$, $V_{GS} = 0 \text{ V}$
Body to drain diode reverse recovery time	t_{rr}	—	130	—	ns	$I_F = 75 \text{ A}$, $V_{GS} = 0 \text{ V}$ $di/dt = 100 \text{ A/ms}$

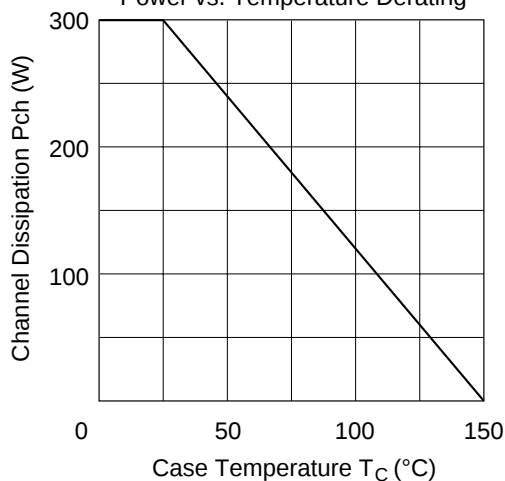
Note: 1. Pulse Test

Mechanical Characteristics

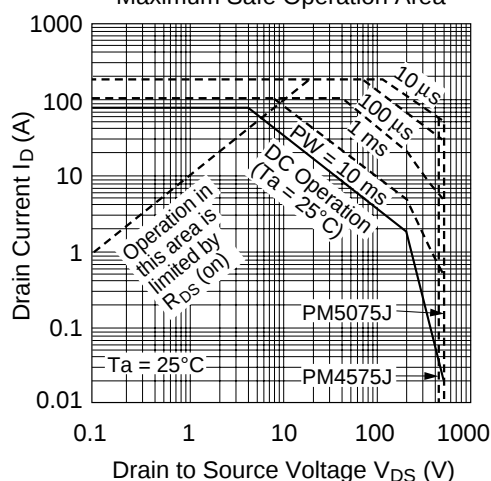
Item	Symbol	Condition	Rating	Unit
Fixing strength	—	Mounting into main-terminal with M4 screw	1.45 to 1.95	N-m
	—	Mounting into heat sink with M5 screw	1.95 to 2.9	N-m
Weight	—	Typical value	200	g

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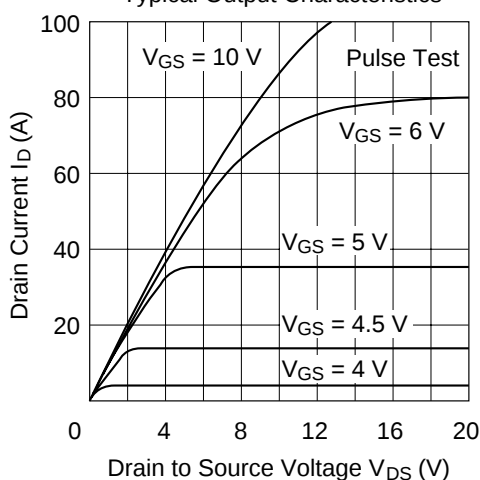
Power vs. Temperature Derating



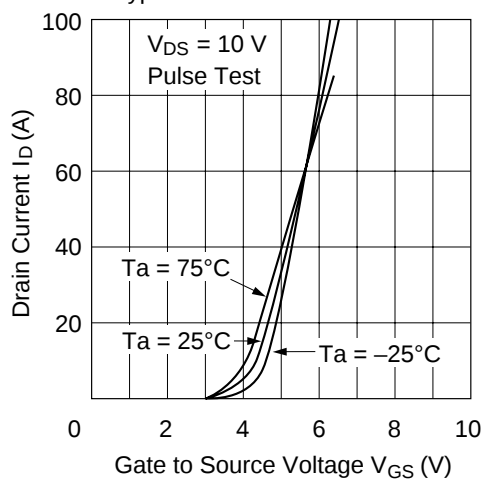
Maximum Safe Operation Area

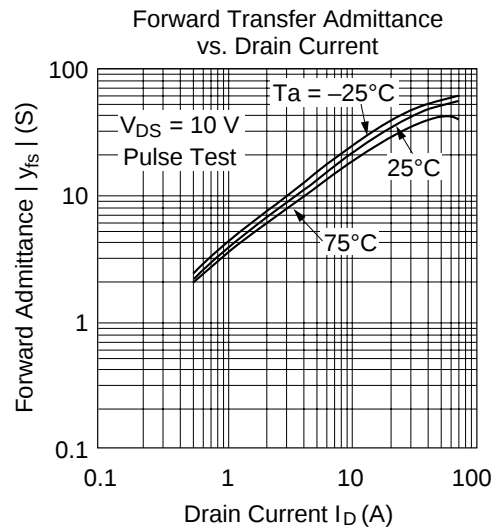
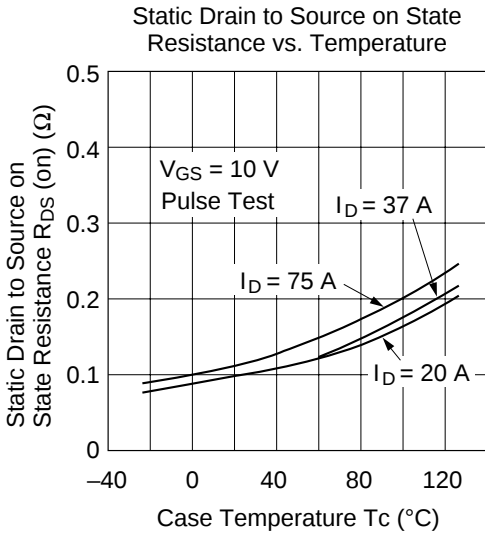
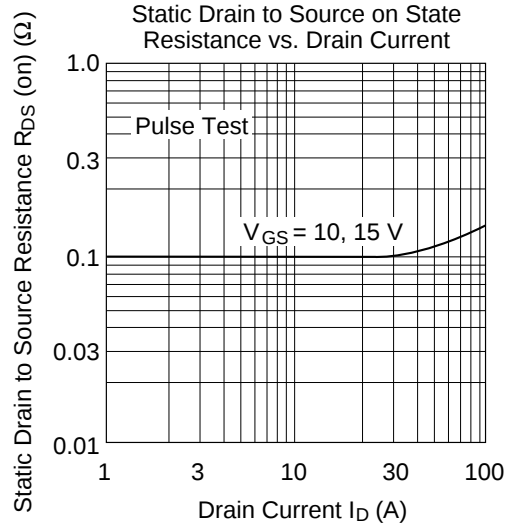
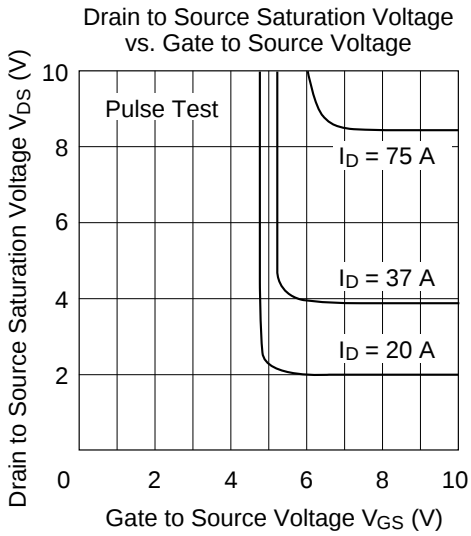


Typical Output Characteristics



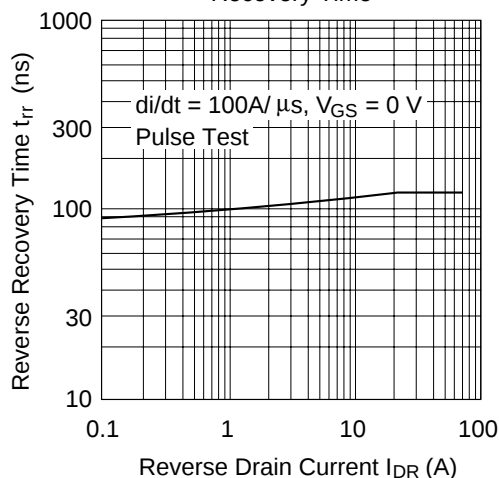
Typical Transfer Characteristics



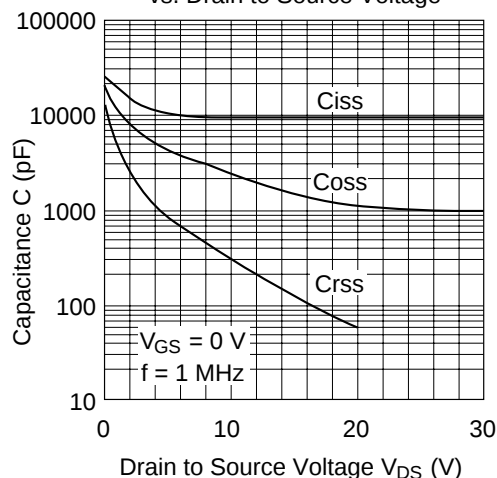


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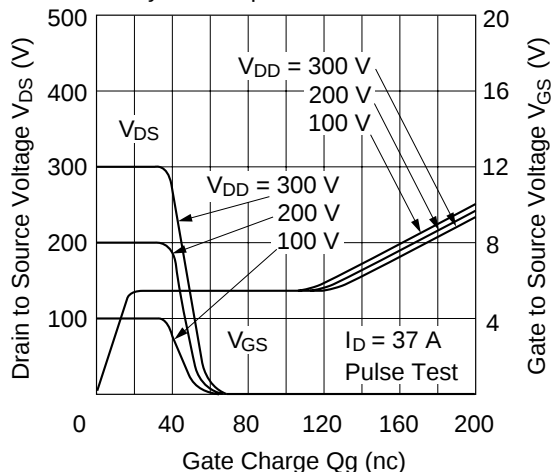
Body to Drain Diode Reverse Recovery Time



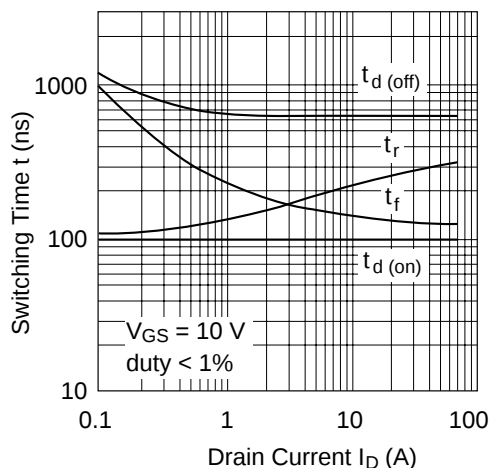
Typical Capacitance vs. Drain to Source Voltage

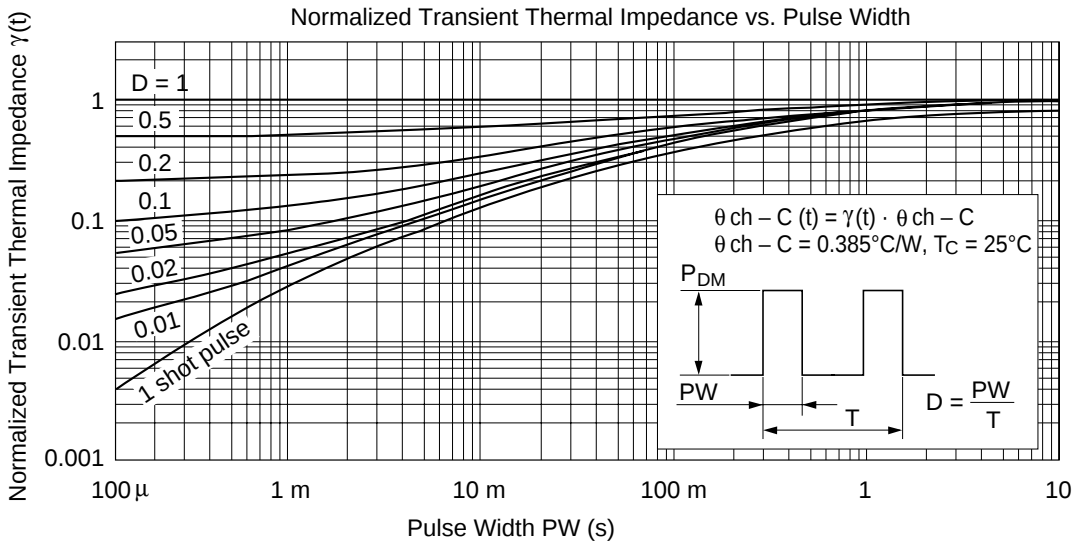
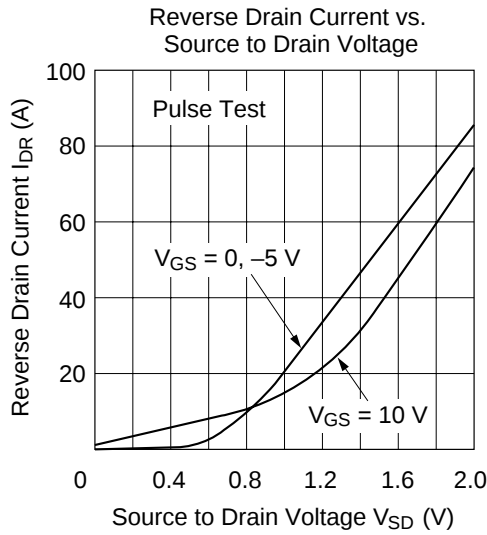


Dynamic Input Characteristics



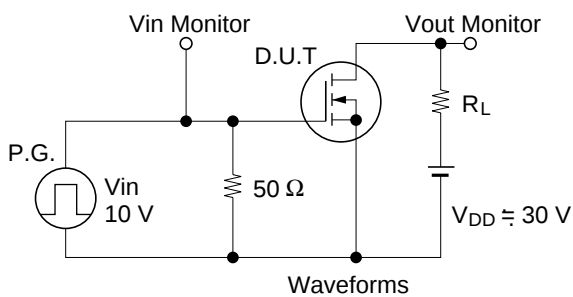
Switching Characteristics



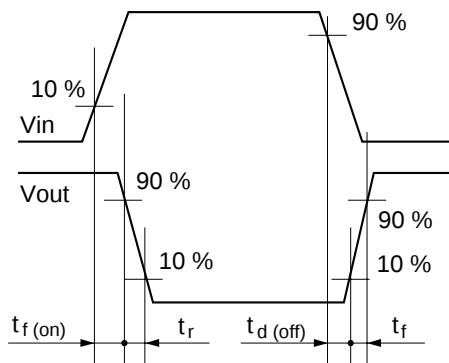


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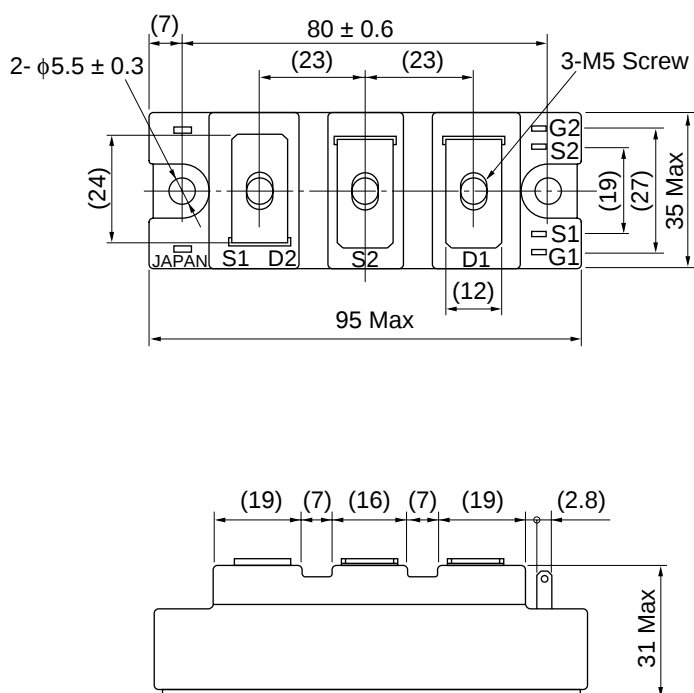
Switching Time Test Circuit



Waveforms



Unit: mm



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